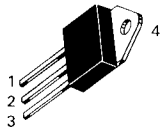


ALPHANUMERIC INDEX — CROSS-REFERENCE (Continued)

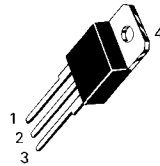
Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number	Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
BU806	BU806		3-380	BUW12A	BUW12A		3-476
BU807	BU807		3-380	BUW13	BUV48P		3-469
BU811		MJE16002	3-976	BUW13A	BUV48A		3-469
BUS12	BUX47		3-499	BUW24	BU326A		3-363
BUS12A	BUX47A		3-499	BUW25	BU326A		3-363
BUS13	BUX48		3-506	BUW26	BUS326A		—
BUS13A	BUX48A		3-506	BUW34	BUX47		3-499
BUS14	BUX98		—	BUW35	BUX47		3-499
BUS14A	BUX98A		—	BUW36	BUX47A		3-499
BUS46P		MJE16002	3-976	BUW44	BUX48		3-506
BUS47	BUX47		3-499	BUW45	BUX48		3-506
BUS47A	BUX47A		3-499	BUW46	BUX48A		3-506
BUS47AP	BUV47A		3-462	BUW72		MJE13008	3-950
BUS47P	BUV47		3-462	BUW74	BUX47		3-499
BUS48	BUX48		3-506	BUW75	BUX47		3-499
BUS48A	BUX48A		3-506	BUW76	BUX47		3-499
BUS48AP	BUV48A		3-469	BUW77	BUX47		3-499
BUS48P	BUV48		3-469	BUW81	MJ10014		3-600
BUS50	BUS50		3-382	BUW81A	MJ10014		3-600
BUS51	BUS51		3-384	BUW84	MJE13003		3-938
BUS52		BUS51	3-384	BUW85	MJE13003		3-938
BUS97	MJ16010		3-758	BUX13	BUX13		3-484
BUS97A	MJ16010A		3-766	BUX14	BUX14		—
BUS98	BUX98		—	BUX14CECCF	BUX14		—
BUS98A	BUX98A		—	BUX14CECCL	BUX14		—
BUT13	BUT13		3-393	BUX15	BUX47A		3-499
BUT14	BUT14		3-399	BUX15CECCF	BUX47A		3-499
BUT15	BUT15		3-405	BUX15CECCL	BUX47A		3-499
BUT33	BUT33		3-411	BUX16	2N6543		3-215
BUT34	BUT34		3-417	BUX16A	2N6543		3-215
BUT35	BUT35		3-423	BUX16B	2N6543		3-215
BUT50P	BUT50P		3-429	BUX16C	2N6543		3-215
BUT51P	BUT51P		3-431	BUX17	BUX48		3-506
BUT90	BUS50		3-382	BUX17A	BUX48		3-506
BUT91	BUS51		3-384	BUX17B	BUX48		3-506
BUT92		BUS51	3-384	BUX17C	BUX48		3-506
BUV10		BUV10N	3-432	BUX18	2N6545		3-221
BUV10N	BUV10N		3-432	BUX18A	2N6545		3-221
BUV11	BUV11		3-435	BUX18B	2N6545		3-221
BUV11N		BUV11	3-435	BUX18C	2N6545		3-221
BUV12	BUV12		3-441	BUX39	BUX39		3-487
BUV18		BUS50	3-382	BUX40	BUX40		3-490
BUV19		BUS50	3-382	BUX41	BUX41		3-493
BUV20	BUV20		3-444	BUX41N		BUX41	3-493
BUV21	BUV21		3-447	BUX42		BUX13	3-484
BUV21N		BUV21	3-447	BUX43		BUX13	3-484
BUV22	BUV22		3-453	BUX47	BUX47		3-499
BUV23	BUV23		3-456	BUX47A	BUX47A		3-499
BUV24		BUS98	3-386	BUX48	BUX48		3-506
BUV25		BUS98A	3-386	BUX48A	BUX48A		3-506
BUV44	BUX47		3-499	BUX48S	BUX48		3-506
BUV45	BUX47A		3-499	BUX66	2N6211		3-161
BUV46	2N6543		3-215	BUX66A	2N6212		3-161
BUV47	BUV47		3-462	BUX66B	2N6212		3-161
BUV47A	BUV47A		3-462	BUX66C	2N6213		3-161
BUV48	BUV48		3-469	BUX67	2N3584		3-20
BUV48A	BUV48A		3-469	BUX67A	2N3584		3-20
BUW11	BUW11		3-476	BUX67B	2N3585		3-20
BUW11A	BUW11A		3-476	BUX67C	2N4240		3-20
BUW12	BUW12		3-476	BUX81		MJ13325	3-700

*Consult Motorola if a direct replacement is necessary.

TABLE 4 — PLASTIC TO-218



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 340-02 (TO-218AC)

I _C Cont Amps Max	V _{CEO} (sus) Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C	
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp			
3	750	MJH16032		4 min	3	2	1.5	2		125	
	850	MJH16034		4 min	3	2	1.5	2		125	
5	400	BUW11		6 min	3	4	0.8	3		125	
	450	BUW11A		6 min	2.5	4	0.8	2.5		125	
		MJH16002		5 min	5	3	0.3	3		100	
		MJH16004		7 min	5	2.7	0.35	3		100	
	500	MJH16002A		5 min	5	3	0.3	3		100	
1500*	MJH12004		2.5 min	4.5	—	1	4.5	4		100	
6	375	BU426†		30 typ	0.6	2 typ	0.5 typ	2.5	6 typ	113	
	400	BU426A†		30 typ	0.6	2 typ	0.5 typ	2.5	6 typ	113	
8	400	BUW12		6 min	6	4	0.8	5		125	
		MJH16106		6/25	8	2 typ	0.1 typ	5		125	
	450	BUW12A		6 min	5	4	0.8	5		125	
		MJH16006		5 min	8	2.5	0.25	5		125	
		MJH16008		7 min	8	2.2	0.25	5		125	
	500	BUT50P##†		30 min	2	0.75 typ	0.1 typ	5		100	
		MJH16006A		5 min	8	2.5	0.25	5		125	
	700	BU508,A		2.25 min	4.5	8 typ	0.5 typ	4.5	7		125
BU508D,AD			2.25 min	4.5	8 typ	0.5 typ	4.5	7		125	
750	MJH12005					0.4 typ	5	4		100	
9	400	BUV47†		7 min	5	2	0.4	6		128	
	450	BUV47A†		7 min	6	2	0.4	6		128	
10	40	TIP33	TIP34	20 min	3				3	80	
	60	BDV65##†	BDV64##†	1k min	5					3	125
		TIP33A	TIP34A	20 min	3					3	80
		TIP140##	TIP145##	500 min	10	2.5 typ	2.5 typ	5	4#		125
	80	BDV65A##†	BDV64A##†	1k min	5					3	125
		TIP33B	TIP34B	20 min	3					3	80
		TIP141##	TIP146##	500 min	10	2.5 typ	2.5 typ	5	4#		125
	100	BDV65B##†	BDV64B##†	1k min	5					3	125
		TIP33C	TIP34C	20 min	3					3	80
		TIP142##	TIP147##	500 min	10	2.5 typ	2.5 typ	5	4#		125
	120	BDV65C##†	BDV64C##†	1k min	5						125
200	BU323P##†		150 min	6	15	15	6			125	
250	BU323AP##†		150 min	6	15	15	6			125	
400	MJH10012##		100/2k	6	15	15	6			118	
800	MJH16018		4 min	5	4.5 typ	0.2 typ	5			150	
15	60	TIP3055	TIP2955	5 min	10				2.5	80	
	150	MJH11018##	MJH11017##	400/15k	10				3#	150	
	200	MJH11020##	MJH11019##	400/15k	10				3#	150	
	250	MJH11022##	MJH11021##	400/15k	10				3#	150	

I_{hfe} (α 1 MHz, ## Darlington

* V_{(BR)CEX} or V_{(BR)CES}

† These devices supplied in Case 340D-01. Consult Motorola for details.

(continued)

TABLE 14 — SWITCHMODE POWER TRANSISTORS (continued)

V _{CEO(sus)} Volts Min	I _C Cont Amps Max	V _{CEV} Volts Min	Device Type NPN unless otherwise noted	h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT	
						t _s μs Max	t _f μs Max	@ I _C Amp				
450	15	1000	BUV48A	8 min	8	2	0.4	10		150	TO-218/340D	
	9	1000 1000	BUS47A BUS47AP	7 min 7 min	5 6	2 2	0.4 0.4	5 6		150 128	TO-204/1 TO-218/340D	
	8	850 850 850 850 850 850 1000	2N6835★ MJE16080 MJ12021★ MJ16006★ MJ16008★ MJH16006★ MJH16008★ BUW12A	7.5/3 5 min 5 min 5 min 7 min 5 min 7 min 6 min	5 8 8 8 8 8 8 5	2.5 2 8 2.5 2.2 2.5 2.2 4	0.25 0.5 0.1 typ 0.25 0.25 0.25 0.25 0.8	5 5 8 5 5 5 5 5	10	80	TO-204/1 TO-220/221A TO-204/1 TO-204/1 TO-204/1 TO-218/340 TO-218/340 TO-218/340	
	5	850 850 850 850 850 850 850 1000	2N6834★ MJ12020★ MJ16002★ MJ16004★ MJE16002★ MJE16004★ MJH16002★ MJH16004★ BUW11A	10/30 5 min 5 min 8 min 5 min 7 min 5 min 7 min 6 min	3 5 5 3 5 5 5 5 2.5	2.7 5 3 2.7 3 2.7 3 2.7 4	0.35 0.13 typ 0.3 0.35 0.3 0.35 0.3 0.35 0.8	3 3 3 3 3 3 3 3 2.5	15	125	TO-204/1 TO-204/1 TO-204/1 TO-204/1 TO-220/221A TO-220/221A TO-218/340 TO-218/340 TO-218/340	
	3	1000	BUX85	30 min	0.1	3.5	1.4	1	4	50	TO-220/221A	
	400	56	600	BUT33##	20 min	36	3.3	1.6	36		250	TO-204/197
		50	650	MJ10015##★	10 min	40	2.5	1	20			TO-204/197
		40	600	MJ10023##★	50/600	10	2.5	0.9	20			TO-204/197
		30	850	BUS98	8 min	20	2.3	0.4	20		250	TO-204/197
		28	600	BUT13##	20 min	20	2.6	0.8	18		175	TO-204/1
		20	500 500 500	MJ10001##★ MJ10005##★ MJ13333★	40/400 40/400 10/60	10 10 5	3 1.5 4	1.8 0.5 0.7	10 10 10	10** 10**		TO-204/1 TO-204/1 TO-204/1
		15	650 650 650 850 850 850	MJ13090★ MJ16110 MJH16110 2N6547★ BUX48 BUV48	8 min 6/20 6/20 6/30 8 min 8 min	10 15 15 10 10 10	2.5 0.8 typ 0.8 typ 4 2 2	0.5 0.1 typ 0.1 typ 0.7 0.4 0.4	10 10 10 10 10 10	6 to 24	175 135 175 150	TO-204/1 TO-204/1 TO-218/340 TO-204/1 TO-204/1 TO-218/340D
		12	700	MJE13009★	6/30	8	3	0.7	8	4**		TO-220/221A
		10	950 550 500 500 450	MJ12010 MJ10012# MJ10003##★ MJ10007##★ MJ13015★	4.2 min 100/2k 30/300 30/300 8/20	5 6 5 5 5	5 6 2.5 1.1 2	1 15 1 0.25 0.5	5 15 5 5 5	6 typ 6 10** 10**		TO-204/1 TO-204/1 TO-204/1 TO-204/1 TO-204/1
		9	850 850	BUS47 BUS47P	7 min 7 min	6 5	2 2	0.4 0.4	6 6		150 128	TO-204/1 TO-218/340D

★ Designers Data Sheet characterization # Darlington ## Darlington with speed-up diode * t_{off} ** |h_{FE}| @ 1 MHz (continued)

2

Designer's Data Sheet
NPN Silicon Power Transistors
Switchmode Series

These transistors are designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switchmode applications.

Typical Applications:

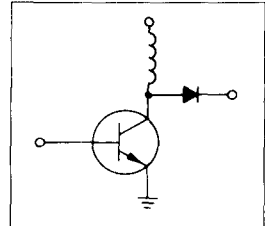
- Switching Regulators
- Inverters
- Solenoids
- Relay Drivers
- Motor Controls
- Deflection Circuits

Features:

- Collector-Emitter Voltage — $V_{CEV} = 850$ and 1000
- Fast Turn-Off Times
 - 140 ns Inductive Fall Time — 100°C (Typ)
 - 170 & 250 ns Inductive Crossover Time — 100°C (Typ)
 - 1200 & 1800 ns Inductive Storage Time — 100°C (Typ)
- 100°C Performance Specified for:
 - Reverse-Biased SOA with Inductive Load
 - Switching Times with Inductive Loads
 - Saturation Voltages
 - Leakage Currents
- Extremely High RBSOA Capability

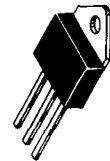
BUW11,A
BUW12,A

POWER TRANSISTORS
5 and 8 AMPERES
400 and 450 VOLTS
125 WATTS



MAXIMUM RATINGS

Rating		Symbol	Value	Unit	
Collector-Emitter Voltage	BUW11/12	$V_{CEO(sus)}$	400	Vdc	
	BUW11A/12A		450		
Collector-Emitter Voltage	BUW11/12	V_{CEV}	850	Vdc	
	BUW11A/12A		1000		
Emitter-Base Voltage		V_{EB}	10	Vdc	
Collector Current — Continuous	BUW11/11A	I_C	5	Adc	
	BUW12/12A		8		
	— Peak (1)	BUW11/11A	I_{CM}		10
		BUW12/12A			20
Base Current — Continuous	BUW11/11A	I_B	2	Adc	
	BUW12/12A		4		
	— Peak (1)	BUW11/11A	I_{BM}		4
		BUW12/12A			8
Total Power Dissipation ($\alpha T_C = 25^{\circ}\text{C}$)		P_D	125	Watts	
$\alpha T_C = 100^{\circ}\text{C}$			50		
Derate above $T_C = 25^{\circ}\text{C}$			1		$\text{W}/^{\circ}\text{C}$
Operating and Storage Junction Temperature Range		T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$	



CASE 340-02
TO-218AC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1	$^{\circ}\text{C}/\text{W}$
Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	275	$^{\circ}\text{C}$

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.

3

BUW11,A • BUW12,A

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS(1)					
Collector-Emitter Sustaining Voltage (Table 1) (I _C = 100 mA, I _B = 0)	BUW11/12 BUW11A/12A V _{CEO(sus)}	400 450	—	—	Vdc
Collector Cutoff Current (V _{CEV} = Rated V _{CEV} , V _{BE(off)} = 1.5 Vdc) (V _{CEV} = Rated V _{CEV} , V _{BE(off)} = 1.5 Vdc, T _C = 100°C)	I _{CEV}	—	—	0.1 1	mAdc
Collector Cutoff Current (V _{CE} = Rated V _{CEV} , R _{BE} = 50 Ω, T _C = 100°C)	I _{CER}	—	—	1	mAdc
Emitter Cutoff Current (V _{EB} = 9 Vdc, I _C = 0)	I _{EBO}	—	—	0.1	mAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased	I _{S/b}	See Figures 8 and 9
Clamped Inductive SOA with Base Reverse Biased	RBSOA	See Figures 10 and 11

BUW11

ON CHARACTERISTICS(1)

Collector-Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.2 Adc) (I _C = 3 Adc, I _B = 0.6 Adc) (I _C = 3 Adc, I _B = 0.6 Adc, T _C = 100°C)	V _{CE(sat)}	—	—	1 1.5 2	Vdc
Base-Emitter Saturation Voltage (I _C = 3 Adc, I _B = 0.6 Adc) (I _C = 3 Adc, I _B = 0.6 Adc, T _C = 100°C)	V _{BE(sat)}	—	—	1.4 1.4	Vdc
DC Current Gain (I _C = 3 Adc, V _{CE} = 5 Vdc)	h _{FE}	6	—	—	—

DYNAMIC CHARACTERISTICS

Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 kHz)	C _{ob}	—	125	—	pF
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SWITCHING CHARACTERISTICS

Inductive Load (Table 1)							
Storage Time	I _C = 3 Adc, I _{B1} = 0.6 Adc, V _{BE(off)} = 5 Vdc, V _{CE(pk)} = 300 Vdc	(T _J = 100°C)	t _{sv}	—	1.2	1.5	μs
Fall Time			t _{fi}	—	0.14	0.3	
Crossover Time			t _c	—	0.25	0.5	
Resistive Load (Table 2)							
Delay Time	I _C = 3 Adc, V _{CC} = 250 Vdc, I _{B1} = 0.6 Adc, PW = 20 μs, Duty Cycle ≤ 2%	(I _{B2} = 0.6 Adc, R _{B2} = 4 Ω)	t _d	—	—	0.1	μs
Rise Time			t _r	—	—	0.8	
Storage Time			t _s	—	—	4	
Fall Time			t _f	—	—	0.8	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

BUW11,A • BUW12,A

ELECTRICAL CHARACTERISTICS (Continued) ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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BUW11A

ON CHARACTERISTICS(1)

Collector-Emitter Saturation Voltage ($I_C = 1\text{ A dc}$, $I_B = 0.2\text{ A dc}$) ($I_C = 2.5\text{ A dc}$, $I_B = 0.5\text{ A dc}$) ($I_C = 2.5\text{ A dc}$, $I_B = 0.5\text{ A dc}$, $T_C = 100^\circ\text{C}$)	$V_{CE(sat)}$	—	—	1 1.5 2	Vdc
Base-Emitter Saturation Voltage ($I_C = 2.5\text{ A dc}$, $I_B = 0.5\text{ A dc}$) ($I_C = 2.5\text{ A dc}$, $I_B = 0.5\text{ A dc}$, $T_C = 100^\circ\text{C}$)	$V_{BE(sat)}$	—	—	1.4 1.4	Vdc
DC Current Gain ($I_C = 2.5\text{ A dc}$, $V_{CE} = 5\text{ Vdc}$)	h_{FE}	6	—	—	—

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 1\text{ kHz}$)	C_{ob}	—	125	—	pF
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SWITCHING CHARACTERISTICS

Inductive Load (Table 1)					
Storage Time	$I_C = 2.5\text{ A dc}$, $I_{B1} = 0.5\text{ A dc}$, $V_{BE(off)} = 5\text{ Vdc}$, $V_{CE(pk)} = 300\text{ Vdc}$	($T_J = 100^\circ\text{C}$)	t_{sv}	—	1.2 1.5
Fall Time			t_{fi}	—	0.14 0.3
Crossover Time			t_c	—	0.25 0.5
Resistive Load (Table 2)					
Delay Time	$I_C = 2.5\text{ A dc}$, $V_{CC} = 250\text{ Vdc}$, $I_{B1} = 0.5\text{ A dc}$, $PW = 20\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$	($I_{B2} = 0.5\text{ A dc}$, $R_{B2} = 4\text{ }\Omega$)	t_d	—	0.1
Rise Time			t_r	—	0.8
Storage Time			t_s	—	4
Fall Time			t_f	—	0.8

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

BUW11,A • BUW12,A

ELECTRICAL CHARACTERISTICS (Continued) (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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BUW12

ON CHARACTERISTICS(1)

Collector-Emitter Saturation Voltage (I _C = 3 Adc, I _B = 0.6 Adc) (I _C = 6 Adc, I _B = 1.2 Adc) (I _C = 6 Adc, I _B = 1.2 Adc, T _C = 100°C)	V _{CE(sat)}	—	—	1 1.5 2	Vdc
Base-Emitter Saturation Voltage (I _C = 6 Adc, I _B = 1.2 Adc) (I _C = 6 Adc, I _B = 1.2 Adc, T _C = 100°C)	V _{BE(sat)}	—	—	1.5 1.5	Vdc
DC Current Gain (I _C = 6 Adc, V _{CE} = 5 Vdc)	h _{FE}	6	—	—	—

DYNAMIC CHARACTERISTICS

Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 kHz)	C _{ob}	—	125	—	pF
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SWITCHING CHARACTERISTICS

Inductive Load (Table 1)							
Storage Time	(I _C = 6 Adc, I _{B1} = 1.2 Adc, V _{BE(off)} = 5 Vdc, V _{CE(pk)} = 300 Vdc)	(T _J = 100°C)	t _{sv}	—	1.8	2.3	μs
Fall Time			t _{fi}	—	0.14	0.3	
Crossover Time			t _c	—	0.17	0.5	
Resistive Load (Table 2)							
Delay Time	(I _C = 6 Adc, V _{CC} = 250 Vdc, I _{B1} = 1.2 Adc, PW = 20 μs, Duty Cycle ≤ 2%)	(I _{B2} = 1.2 Adc, R _{B2} = 4 Ω)	t _d	—	—	0.1	μs
Rise Time			t _r	—	—	0.8	
Storage Time			t _s	—	—	4	
Fall Time			t _f	—	—	0.8	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

BUW12A

ON CHARACTERISTICS(1)

Collector-Emitter Saturation Voltage (I _C = 3 Adc, I _B = 0.6 Adc) (I _C = 5 Adc, I _B = 1 Adc) (I _C = 5 Adc, I _B = 1 Adc, T _C = 100°C)	V _{CE(sat)}	—	—	1 1.5 2	Vdc
Base-Emitter Saturation Voltage (I _C = 5 Adc, I _B = 1 Adc) (I _C = 5 Adc, I _B = 1 Adc, T _C = 100°C)	V _{BE(sat)}	—	—	1.5 1.5	Vdc
DC Current Gain (I _C = 5 Adc, V _{CE} = 5 Vdc)	h _{FE}	6	—	—	—

DYNAMIC CHARACTERISTICS

Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 kHz)	C _{ob}	—	125	—	pF
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SWITCHING CHARACTERISTICS

Inductive Load (Table 1)							
Storage Time	(I _C = 5 Adc, I _{B1} = 1 Adc, V _{BE(off)} = 5 Vdc, V _{CE(pk)} = 300 Vdc)	(T _J = 100°C)	t _{sv}	—	1.8	2.3	μs
Fall Time			t _{fi}	—	0.14	0.3	
Crossover Time			t _c	—	0.17	0.5	
Resistive Load (Table 2)							
Delay Time	(I _C = 5 Adc, V _{CC} = 250 Vdc, I _{B1} = 1 Adc, PW = 20 μs, Duty Cycle ≤ 2%)	(I _{B2} = 1 Adc, R _{B2} = 4 Ω)	t _d	—	—	0.1	μs
Rise Time			t _r	—	—	0.8	
Storage Time			t _s	—	—	4	
Fall Time			t _f	—	—	0.8	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

TYPICAL STATIC CHARACTERISTICS

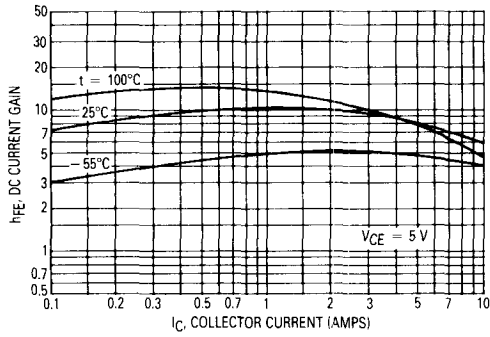


Figure 1. Typical DC Current Gain

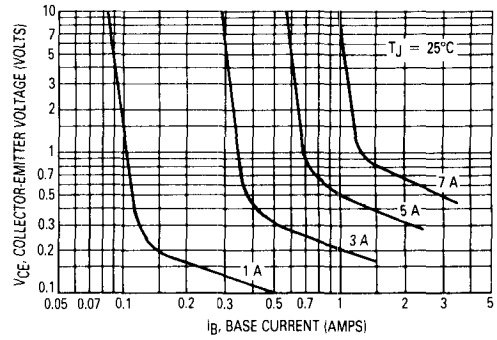


Figure 2. Typical Collector Saturation Region

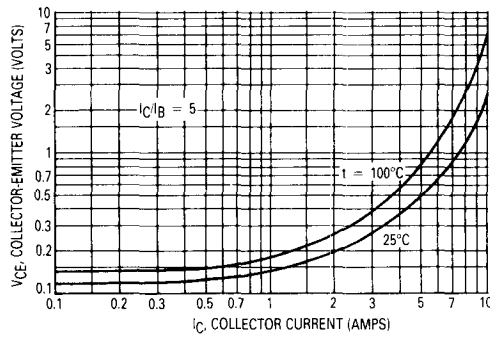


Figure 3. Typical Collector Saturation Region

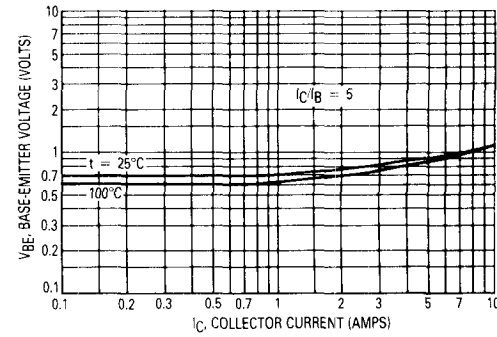


Figure 4. Typical Base-Emitter Voltage

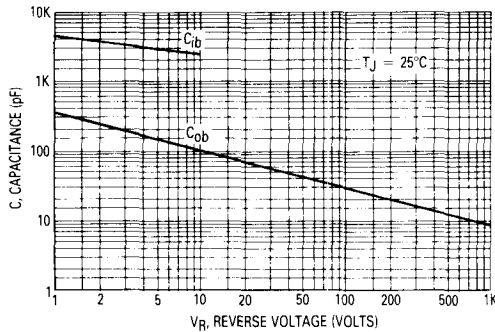


Figure 5. Typical Capacitance

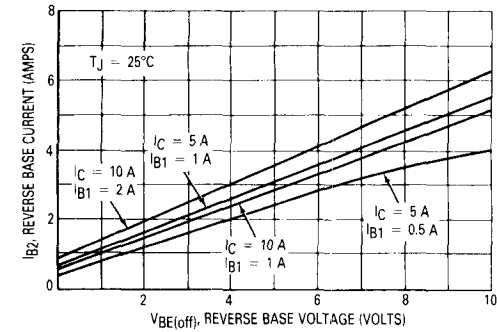


Figure 6. Peak Reverse Base Current

3

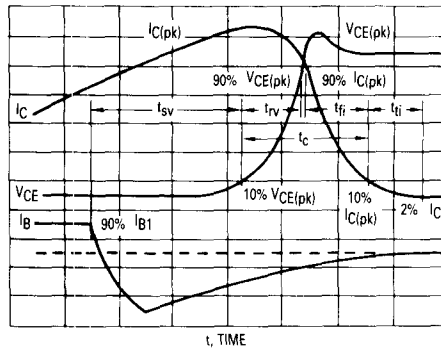


Figure 7. Inductive Switching Measurements

Table 1. Inductive Load Switching

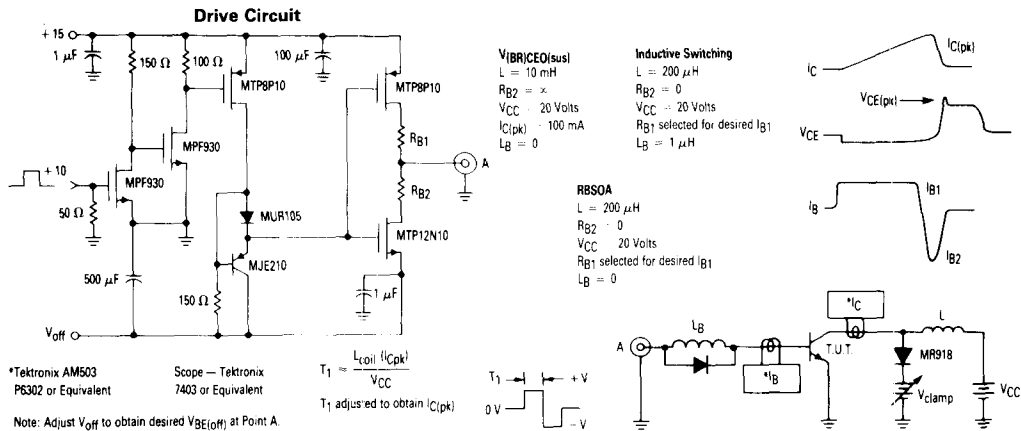
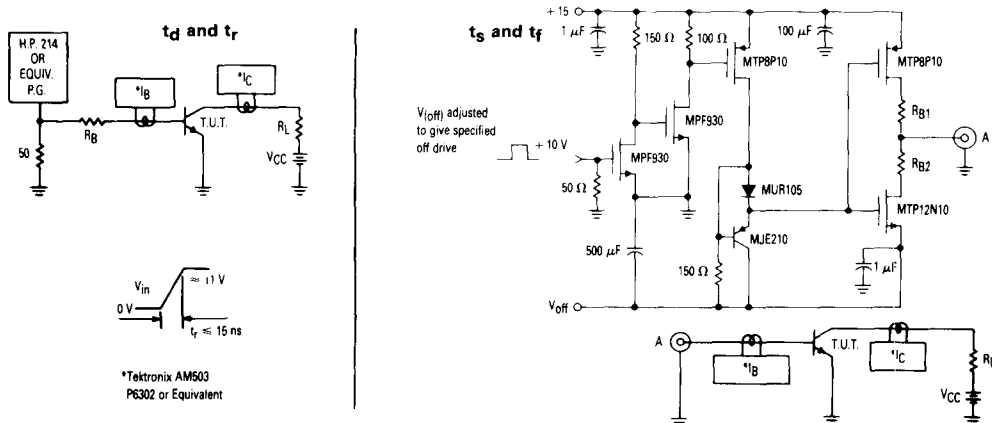


Table 2. Resistive Load Switching



BUW11,A • BUW12,A

MAXIMUM FORWARD BIAS SAFE OPERATING AREA

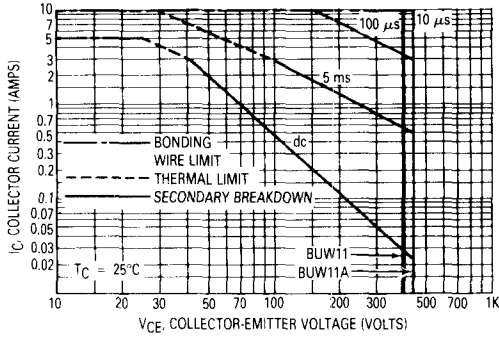


Figure 8. BUW11,A

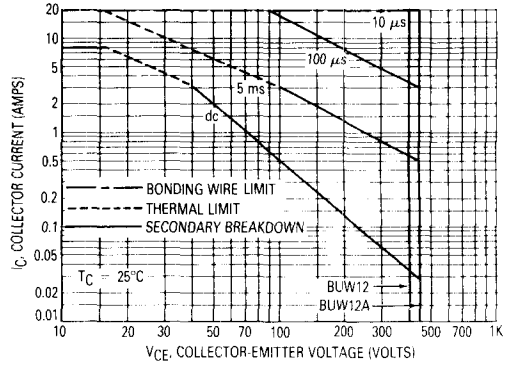


Figure 9. BUW12,A

MAXIMUM REVERSE BIAS SAFE OPERATING AREA

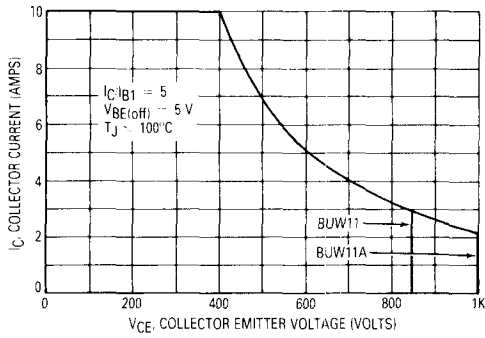


Figure 10. BUW11,A

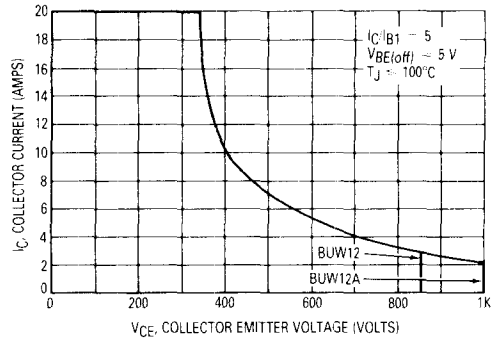


Figure 11. BUW12,A

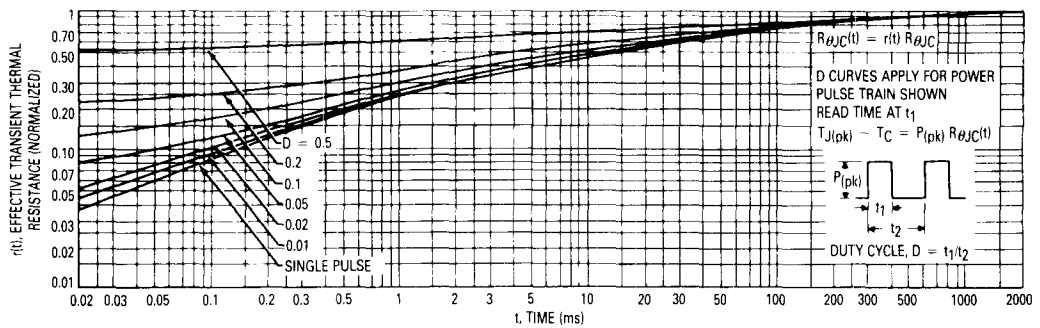


Figure 12. Thermal Response

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SAFE OPERATING AREA INFORMATION

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 8 and 9 is based on $T_C = 25^\circ\text{C}$; $T_J(pk)$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figures 8 and 9 may be found at any case temperature by using the appropriate curve on Figure 13.

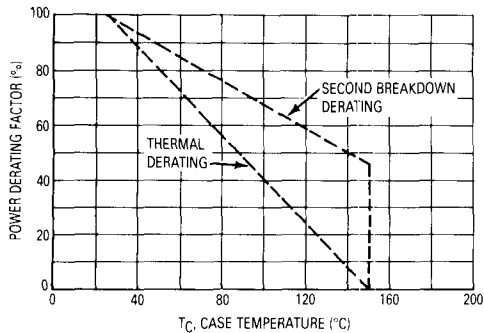


Figure 13. Power Derating

$T_J(pk)$ may be calculated from the data in Figure 12. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base-to-emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Biased Safe Operating Area and represents the voltage-current condition allowable during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figures 10 and 11 gives the RBSOA characteristics.

OUTLINE DIMENSIONS

